

650 V, 50 mΩ Gallium Nitride (GaN) FET 20 March 2020

1. General description

The GAN063-650WSA is a 650 V, 50 m Ω Gallium Nitride (GaN) FET. It is a normally-off device that combines Nexperia's state-of-the-art high-voltage GaN HEMT and low-voltage silicon MOSFET technologies — offering superior reliability and performance.

2. Features and benefits

- Ultra-low reverse recovery charge
- Simple gate drive (0 V to +10 V or 12 V)
- Robust gate oxide (±20 V capability)
- High gate threshold voltage (+4 V) for very good gate bounce immunity
- Very low source-drain voltage in reverse conduction mode
- Transient over-voltage capability (800 V)

3. Applications

- Hard and soft switching converters for industrial and datacom power
- Bridgeless totempole PFC
- PV and UPS inverters
- Servo motor drives

4. Quick reference data

| Table 1. Qui | ick reference data | | | | | |
|---------------------|----------------------------------|--|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | -55 °C ≤ T _j ≤ 175 °C | - | - | 650 | V |
| ID | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | - | 34.5 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | - | 143 | W |
| Tj | junction temperature | | -55 | - | 175 | °C |
| Static chara | acteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C | - | 50 | 60 | mΩ |
| Dynamic cl | haracteristics | | | | | |
| Q _{GD} | gate-drain charge | $I_D = 25 \text{ A}; V_{DS} = 400 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 4 | - | nC |
| Q _{G(tot)} | total gate charge | T _j = 25 °C | - | 15 | - | nC |
| Source-dra | in diode | | | | | |
| Qr | recovered charge | $I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -1000 \text{ A}/\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 400 \text{ V}; \frac{\text{Fig. 14}}{14}$ | - | 125 | - | nC |

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5. Pinning information

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6. Ordering information

| Type number | Package | | | | | | |
|---------------|---------|--|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| GAN063-650WSA | | plastic, single-ended through-hole package; 3 leads; 5.45 mm pitch; 20.45 mm x 15.6 mm x 4.95 mm body | SOT429 | | | | |

7. Marking

| Table 4. Marking codes | | | | | | |
|------------------------|---------------|--|--|--|--|--|
| Type number | Marking code | | | | | |
| GAN063-650WSA | GAN063-650WSA | | | | | |

8. Limiting values

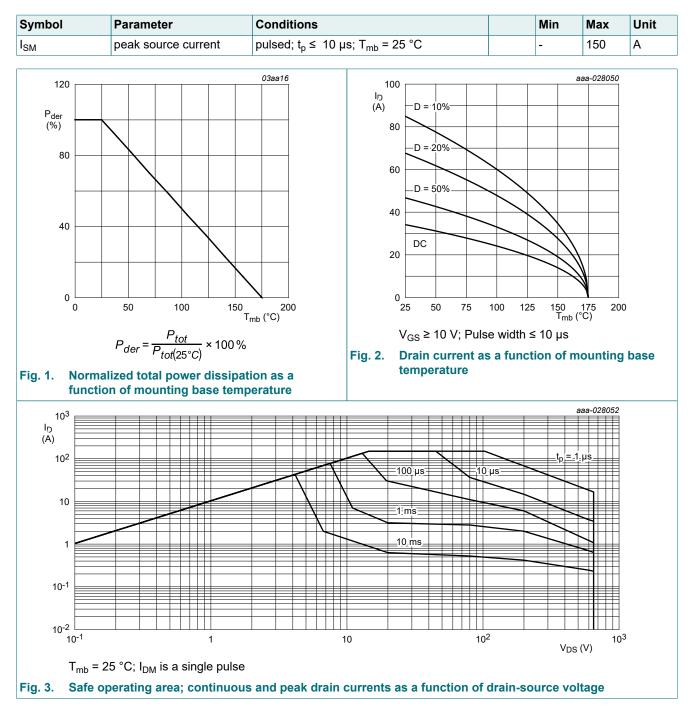
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|-----------------------------------|--|-----|------|------|
| V _{DS} | drain-source voltage | -55 °C ≤ T _j ≤ 175 °C | - | 650 | V |
| V _{TDS} | transient drain to source voltage | pulsed; $t_p = 1 \ \mu s$; $\delta_{factor} = 0.01$ | - | 800 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 143 | W |
| ID | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | 34.5 | А |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | - | 24.4 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | - | 150 | А |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |
| Source-drai | n diode | · · · · · · | I | | |
| I _S | source current | T _{mb} = 25 °C; V _{GS} = 0 V | - | 34.5 | А |

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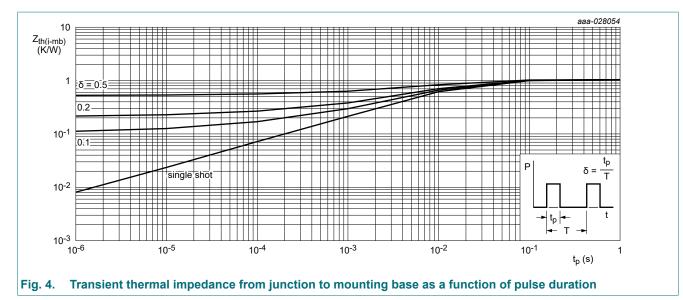


9. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|----------------------|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 4</u> | - | - | 1.05 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | vertical in free air | - | - | 40 | K/W |

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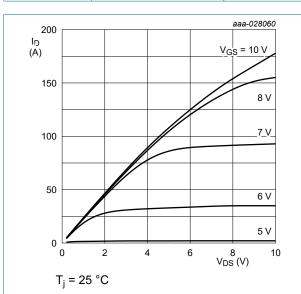


10. Characteristics

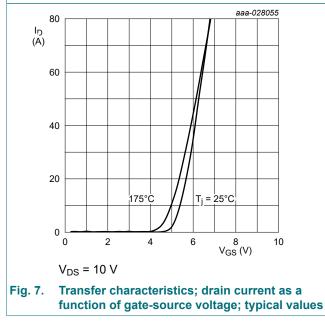
| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|---------------------|--|--|-----|------|-----|------|
| Static chara | acteristics | · · · | | | | |
| V _{GS(th)} | gate-source threshold | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C | 3.4 | 3.9 | 4.5 | V |
| | voltage | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u> | 2.2 | - | - | V |
| | | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u> | - | - | 5.2 | V |
| I _{DSS} | drain leakage current | V _{DS} = 650 V; V _{GS} = 0 V; T _j = 25 °C | - | 2 | 25 | μA |
| | | V _{DS} = 650 V; V _{GS} = 0 V; T _j = 175 °C | - | 25 | - | μA |
| I _{GSS} | gate leakage current | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 10 | 100 | nA |
| | | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 10 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C | - | 50 | 60 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 10 | - | 120 | - | mΩ |
| R _G | gate resistance | f = 1 MHz | - | 2.3 | - | Ω |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 25 A; V _{DS} = 400 V; V _{GS} = 10 V; | - | 15 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 6 | - | nC |
| Q _{GD} | gate-drain charge | | - | 4 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 400 V; V _{GS} = 0 V; f = 1 MHz; | - | 1000 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 11</u> | - | 130 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 8 | - | pF |
| C _{o(er)} | effective output capacitance, energy related | $0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ T _j = 25 °C; <u>Fig. 12</u> | - | 190 | - | pF |
| C _{o(tr)} | effective output capacitance, time related | $0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ T _j = 25 °C | - | 310 | - | pF |

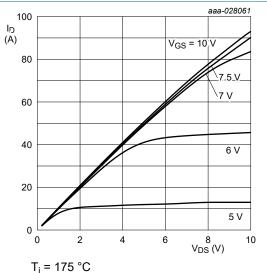
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------|---|-----|------|-----|------|
| t _{d(on)} | turn-on delay time | $V_{DS} = 400 \text{ V}; \text{ R}_{L} = 16 \Omega; \text{ V}_{GS} = 12 \text{ V};$ $\text{R}_{G(ext)} = 40 \Omega$ | - | 57 | - | ns |
| t _r | rise time | | - | 10 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 88 | - | ns |
| t _f | fall time | | - | 11 | - | ns |
| Q _{oss} | output charge | V _{GS} = 0 V; V _{DS} = 400 V | - | 125 | - | nC |
| Source-dra | in diode | | | | | |
| V _{SD} | source-drain voltage | I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 13</u> | - | 1.9 | - | V |
| | | I _S = 12.5 A; V _{GS} = 0 V; T _j = 25 °C | - | 1.35 | - | V |
| t _{rr} | reverse recovery time | $\label{eq:IS} \begin{array}{l} I_{S} = 25 \text{ A}; \ dI_{S}/dt = -1000 \text{ A}/\mu\text{s}; \\ V_{GS} = 0 \text{ V}; \ V_{DS} = 400 \text{ V}; \ \overline{\text{Fig. } 14} \end{array}$ | - | 54 | - | ns |
| Q _r | recovered charge | | - | 125 | - | nC |



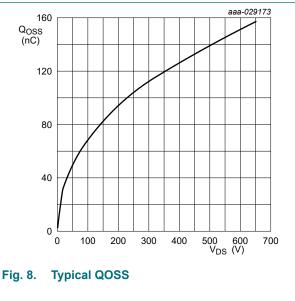




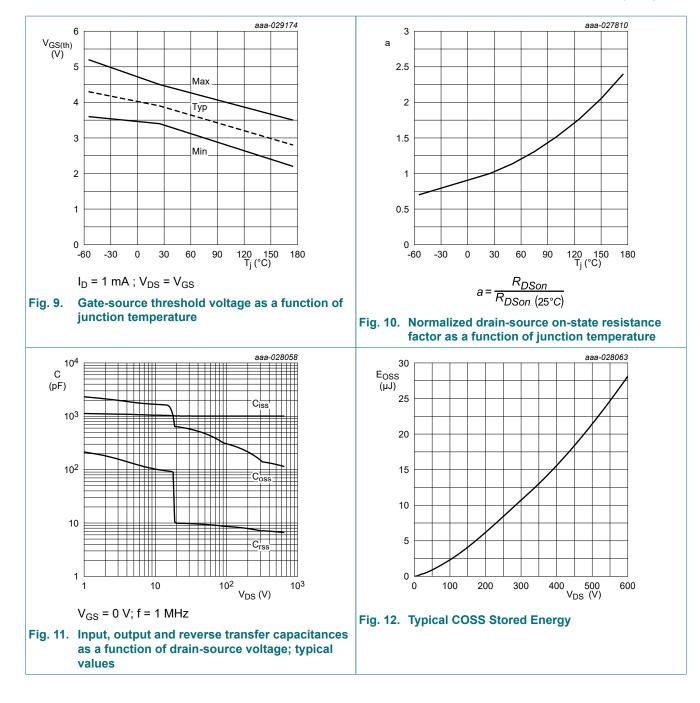




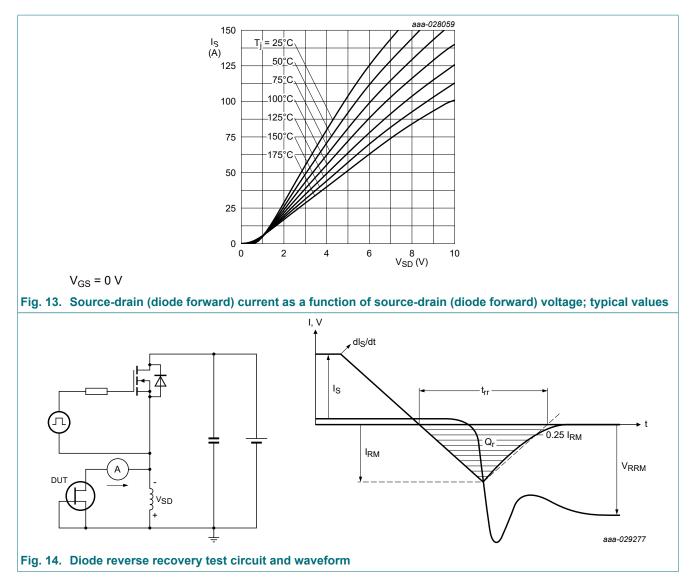




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11. Application information

To achieve maximum efficiency and stability when switching high currents, a switching node RC snubber (R_{sn} , C_{sn}) is recommended. For $I_L < 14$ A, a switching-node snubber is not required.

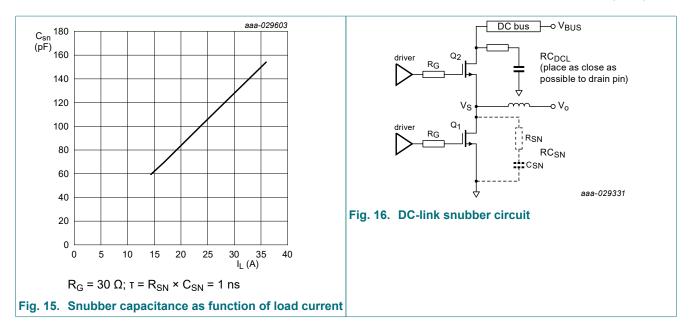
C_{SN} is taken from the graph.

 R_{SN} should be selected to achieve a time constant of 1 ns; e.g. if C_{SN} = 100 pF, R_{SN} = 1 ns / 100 pF = 10 $\Omega.$

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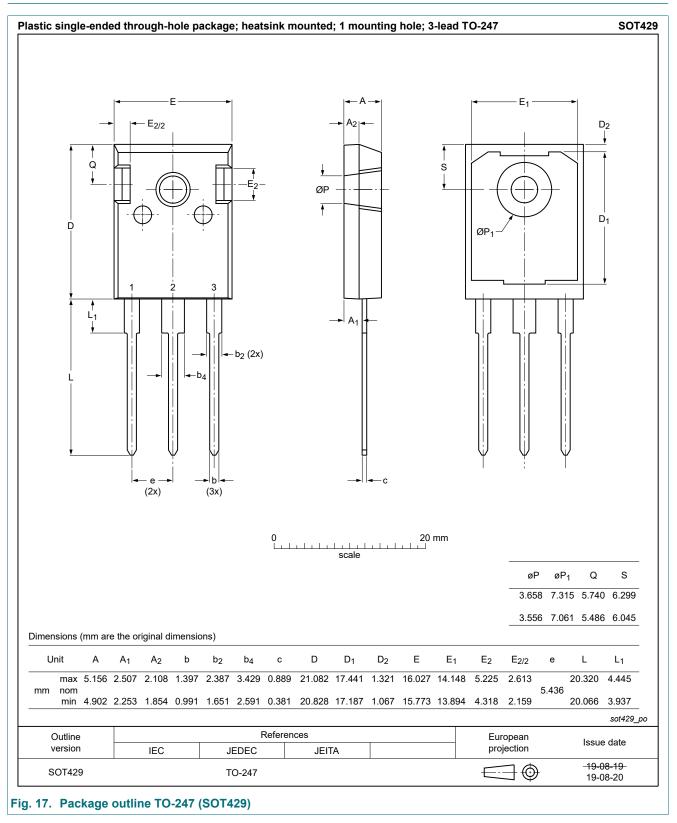


Note: A DC-link snubber is recommended in all cases. Optimal is 20 nF in series with 4 Ω , most easily achieved with parallel combination 10 nF and 8 Ω . This snubber lowers the Q factor of any resonance in the bus. That resonance will act as a load on the high gain amplifier that is the GaN FET and can lead to instability. For very high current, an RC snubber is recommended for the switching node. This will increase switching loss, so this is only recommended at high power levels where the losses are a very small percentage of the total power.

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12. Package outline



13. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|-----------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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- [2] The term 'short data sheet' is explained in section "Definitions".
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